

ABSTRACTPROCESS FOR FORMING DEPOSITED FILM AND PROCESS
FOR PREPARING SEMICONDUCTOR DEVICE

A deposited film formation method comprises the steps of:

(a) feeding a gas of an organometallic compound containing molybdenum atom and hydrogen gas onto a substrate having an electron donative surface; and

(b) maintaining the temperature of the electron donative surface within the range of the decomposition temperature of the organometallic compound or lower and 800 °C or lower to form a molybdenum film on the electron donative surface.

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This Sheet Has Been Replaced

